



Silicon Carbide Schottky Diode S1S12020RB1

V_{RRM}	=	1200 V
$I_F (T_C=135^\circ C)$	=	32 A
Q_C	=	107 nC

Features

- 1200V Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching

Package



Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway



Applications

- Switch Mode Power Supplies (SMPS)
- Power Factor Correction
- Motor Drives

Part Number	Package
S1S12020RB1	TO247-2L

料号: 3960230000
 品名: SiC SBD塑封器件 1200V 20A-T0247-2L(S1S12020RB1)
 版本: 01
 编辑: 温小花 2025.01.02
 审核: 王松 2025.01.02



Maximum Rated Values (T_c=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	1200	V		
V _R	DC Peak Reverse Voltage	1200	V		
I _F	Continuous Forward Current	67	A	T _c =25°C	Fig. 3
		32		T _c =135°C	
		23		T _c =150°C	
I _{FRM}	Repetitive Peak Forward Surge Current	91	A	T _c =25°C, t _p =10 ms, Half Sine Pulse	
		77		T _c =110°C, t _p =10 ms, Half Sine Pulse	
I _{FSM}	Non-Repetitive Forward Surge Current	98	A	T _c =25°C, t _p =10 ms, Half Sine Pulse	
		84		T _c =110°C, t _p =10 ms, Half Sine Pulse	
I _{F,MAX}	Non-Repetitive Forward Surge Current	872	A	T _c =25°C, t _p =10μs, Square Wave Pulse	
		753		T _c =110°C, t _p =10μs, Square Wave Pulse	
P _{tot}	Power Dissipation	319	W	T _c =25°C	Fig. 4
		138		T _c =110°C	
T _J	Operating Temperature	-55 to +175	°C		
T _{stg}	Storage Temperature	-55 to +175	°C		
	TO-247 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	

Electrical Characteristics (T_J=25°C)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
V _F	Forward Voltage		1.4	1.9	V	I _F =20A, T _J =25°C	Fig. 1
			1.9			I _F =20A, T _J =175°C	
I _R	Reverse Current		9.6	200	μA	V _R =1200V, T _J =25°C	Fig. 2
			147			V _R =1200V, T _J =175°C	
Q _C	Total Capacitive Charge		107		nC	V _R =800V, T _J =25°C	Fig. 5
C	Total Capacitance		1615		pF	V _R =0V, T _J =25°C, f=1MHz	Fig. 6
			94			V _R =400V, T _J =25°C, f=1MHz	
			88			V _R =800V, T _J =25°C, f=1MHz	
E _C	Capacitance Stored Energy		27		μJ	V _R =800 V	Fig. 7

Thermal Characteristics

Symbol	Parameter	Value	Unit	Note
R _{θJC}	Thermal Resistance(Junction to Case)	0.47	°C/W	Fig. 8



Typical Performance

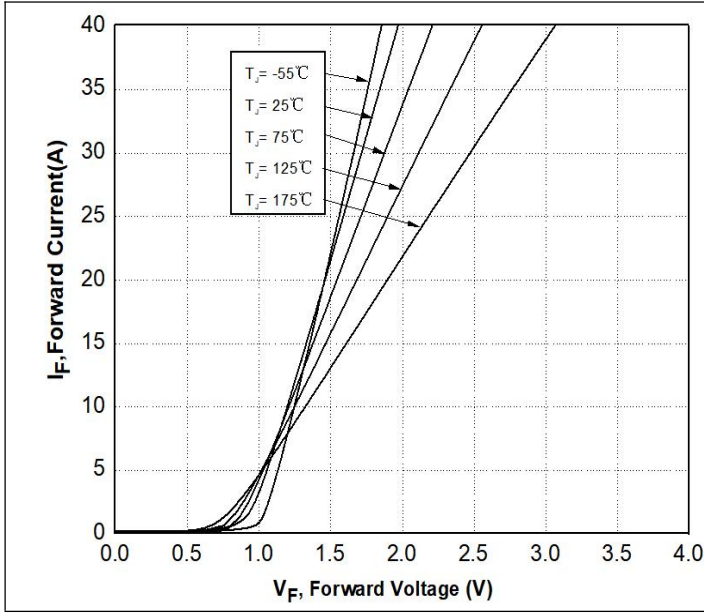


Figure 1. Forward Characteristics

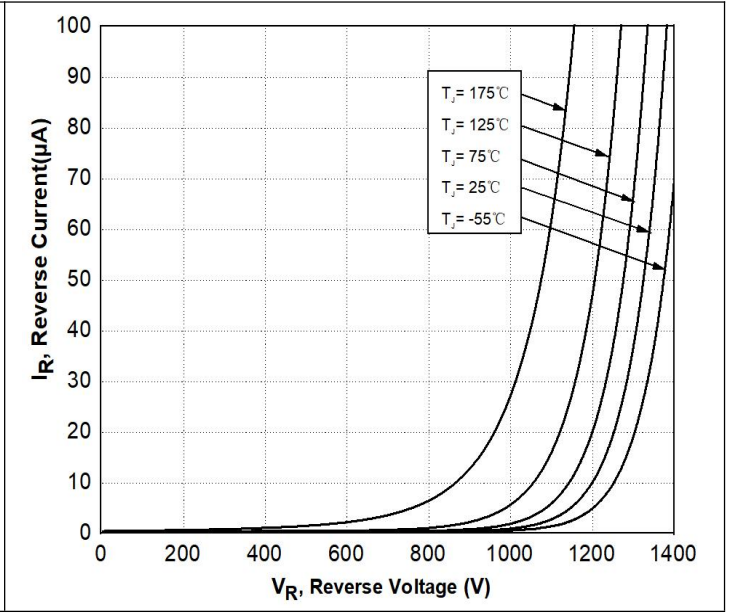


Figure 2. Reverse Characteristics

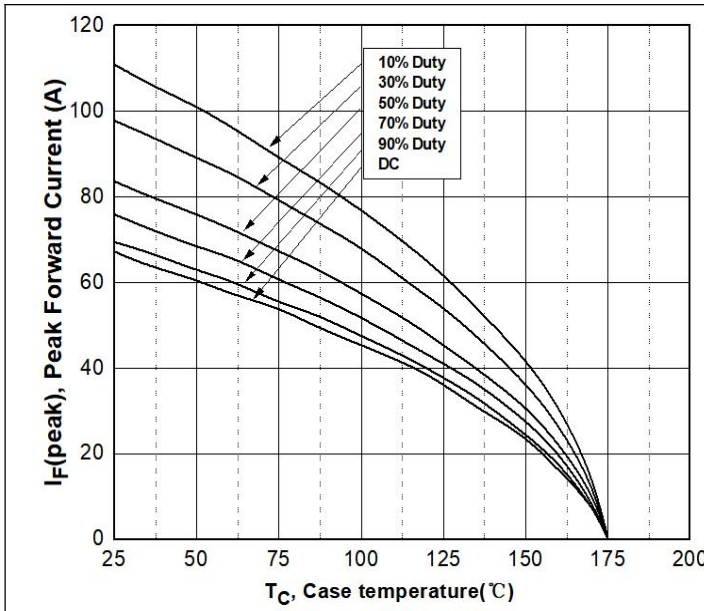


Figure 3. Current Derating

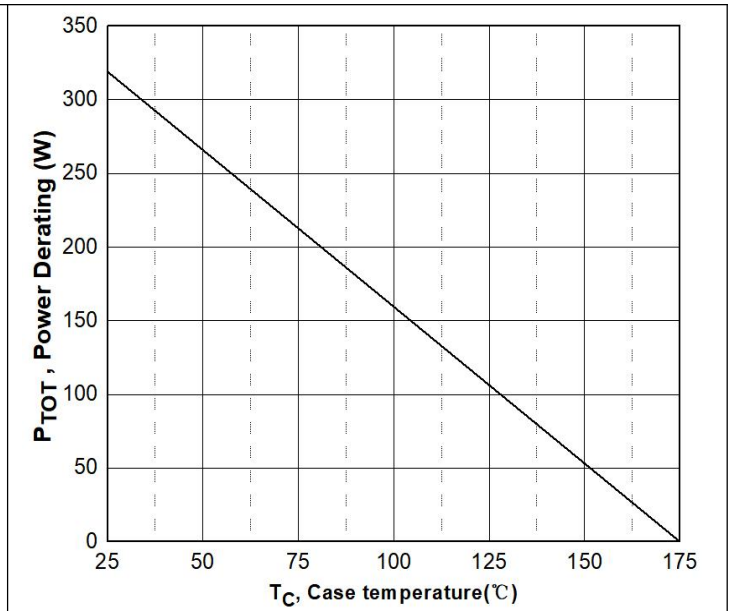


Figure 4. Power Derating



Typical Performance

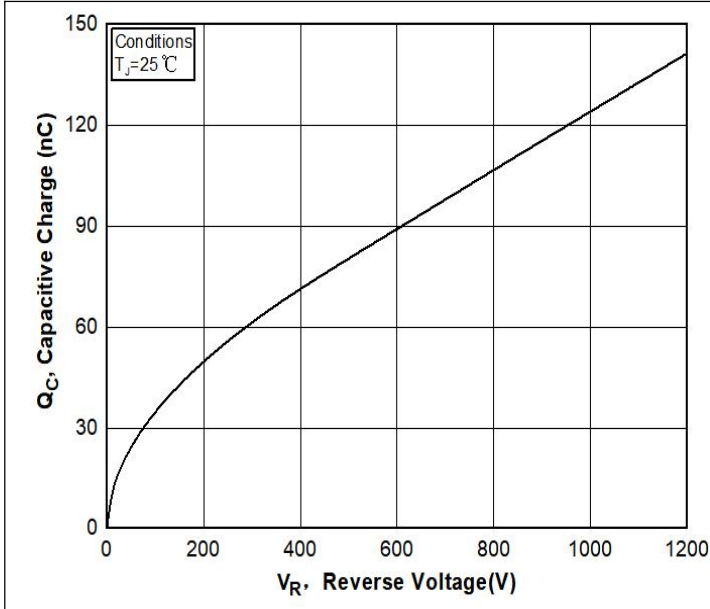


Figure 5. Capacitance Charge Vs. Reverse Voltage

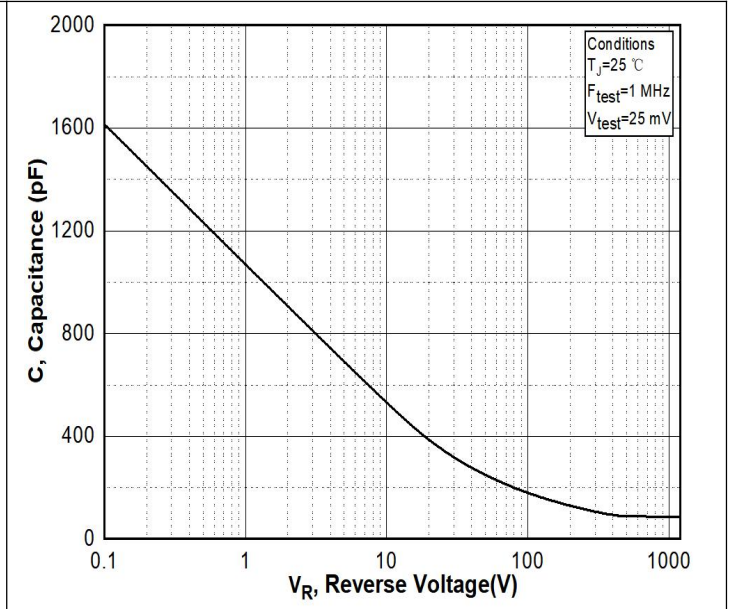


Figure 6. Capacitance Vs. Reverse Voltage

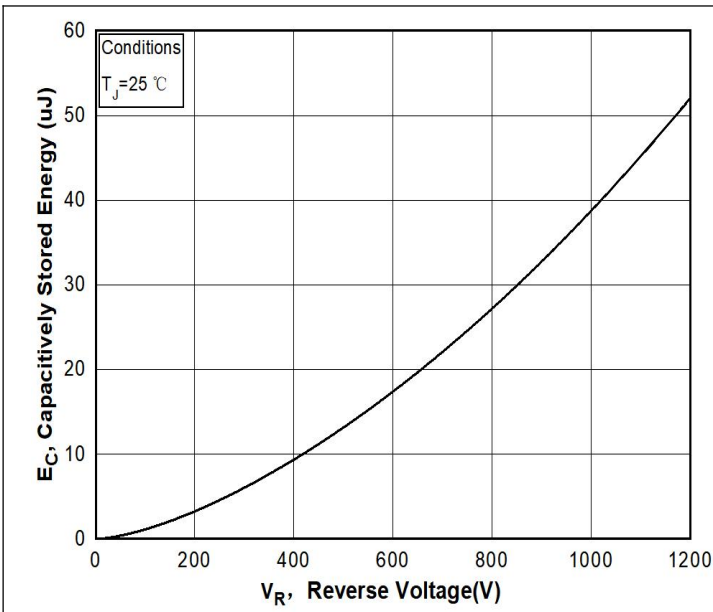


Figure 7. Capacitance Stored Energy

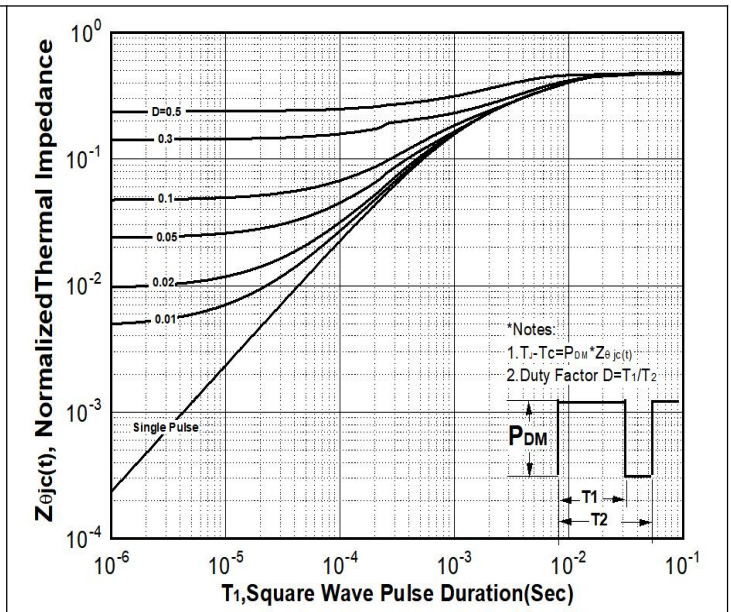
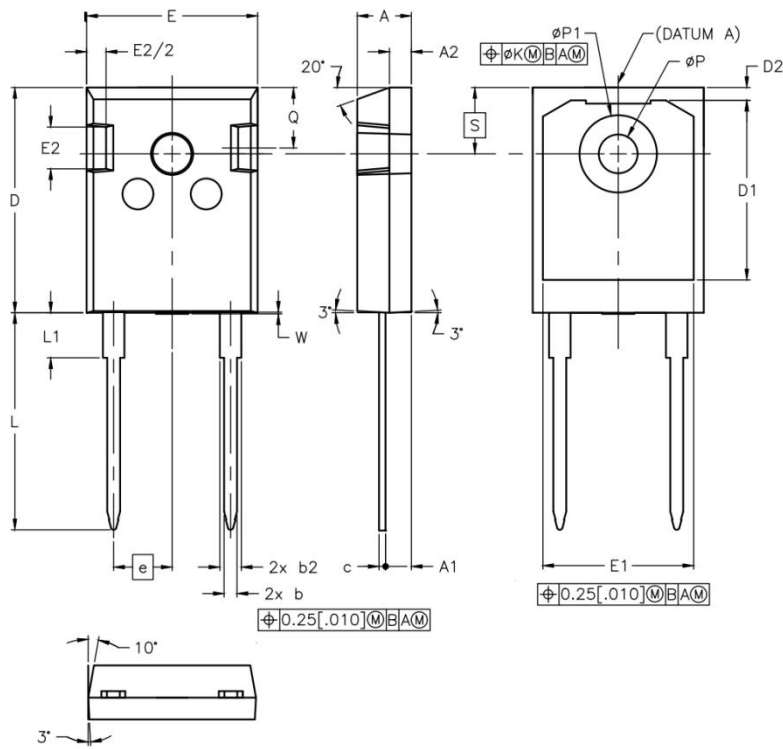


Figure 8. Transient Thermal Response Curve(Junction-to-Case)



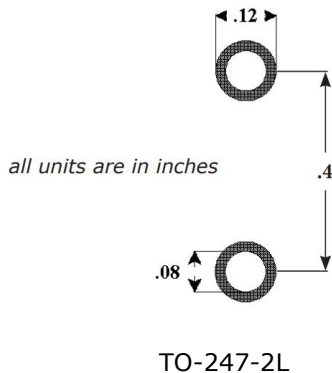
Package Dimensions

Package TO-247-2L



POS	Inches		Millimeters	
	Min	Max	Min	Max
A	.190	.205	4.70	5.31
A1	.087	.102	2.21	2.59
A2	.059	.098	1.50	2.49
b	.039	.055	0.99	1.40
b2	.065	.094	1.65	2.39
c	.015	.035	0.38	0.89
D	.819	.845	20.80	21.46
D1	.515	-	13.08	-
D2	.020	.053	0.51	1.35
E	.620	.640	15.49	16.26
E1	.530	-	13.46	-
E2	.135	.157	3.43	3.99
e	.214		5.44	
ØK	.010		0.25	
L	.780	.800	19.81	20.32
L1	-	.177	-	4.50
ØP	.140	.144	3.56	3.66
ØP1	.278	.291	7.06	7.39
Q	.212	.244	5.38	6.20
S	.243		6.17	
W	-	.006	-	0.15

Recommended Solder Pad Layout



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